

1SS226

PRV : 85 Volts
Io : 100 mA

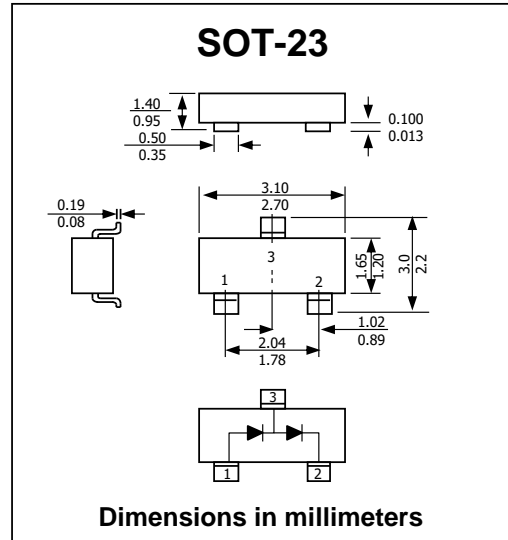
FEATURES :

- * Small package
- * Low forward voltage
- * Fast reverse recovery time
- * Small total capacitance
- * Ultra high speed switching application
- * Pb / RoHS Free

MECHANICAL DATA :

- * Case : SOT-23 plastic Case
- * Marking Code : A7

SILICON EPITAXIAL PLANAR DIODE



MAXIMUM RATINGS AND THERMAL CHARACTERISTICS (Ta = 25 °C)

Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Maximum Peak Forward Current	I_{FM}	300	mA
Average Forward Current	$I_{F(AV)}$	100	mA
Surge Current (10 ms)	I_{FSM}	2	A
Power Dissipation	P_D	350	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Typical Thermal Resistance Junction to Ambient ¹⁾	$R_{\theta JA}$	357	°C/W

¹⁾ Device mounted on FR-4 substrate PC board, with minimum recommended pad layout.

ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

Parameter	Test Condition	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage	$I_R = 10 \mu A$	$V_{(RB)R}$	80	-	V
Forward Voltage	$I_F = 100 mA$	V_F	-	1.2	V
Reverse Current	$V_R = 80 V$	I_R	-	0.5	μA
Total Capacitance	$V_R = 0 V, f = 1 MHz$	C_T	-	3	pF
Reverse Recovery Time	$I_R = 10 mA$	T_{rr}	-	4	ns



RATINGS AND CHARACTERISTIC CURVES (1SS226)

Fig 1. Power Derating Curve

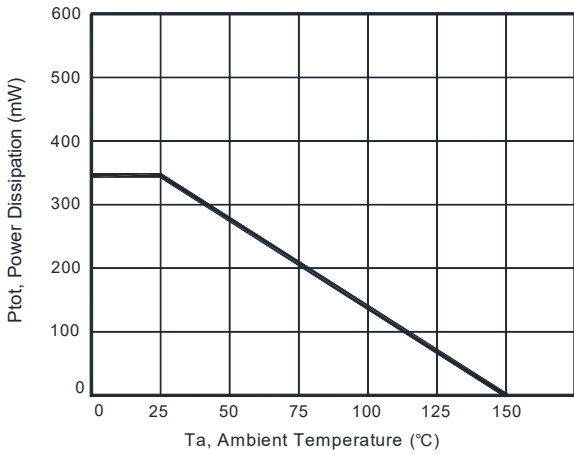


Fig 2. Capacitance Characteristics

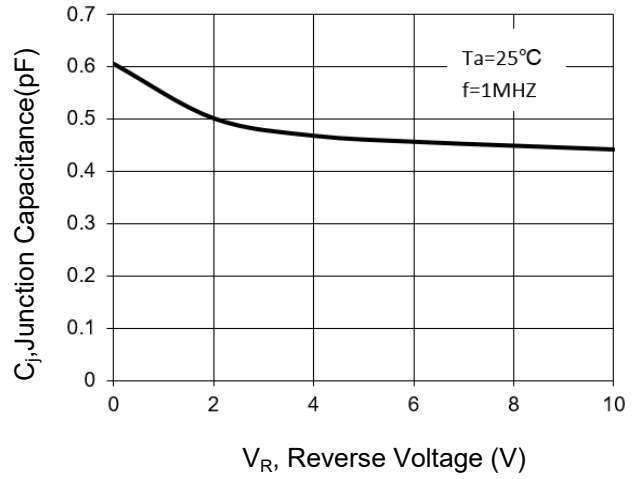


Fig 3. Reverse Characteristics

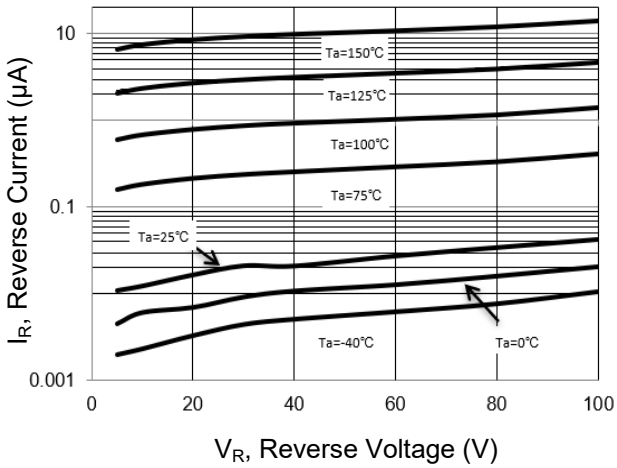


Fig 4. Forward Characteristics

